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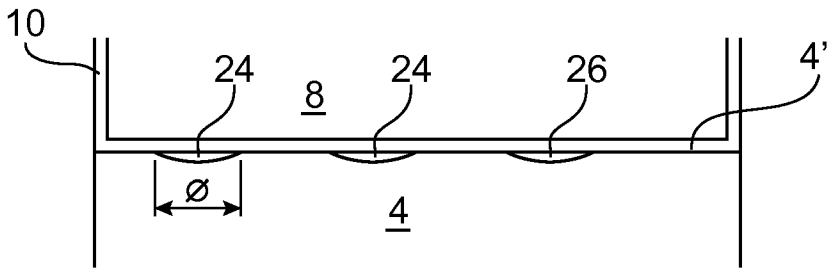


FIG.2B

(57) Abstract: The invention concerns a process of preparing a thin layer to be transferred onto a substrate (8) having a surface topology, and therefore variations in altitude or level, in a direction perpendicular to a plane defined by the thin layer, this process comprising the formation, on the thin layer, of a layer (4) of adhesive material, the thickness of which enables to carry out a plurality of polishing steps of its surface in order to eliminate any defect or void (24, 26), or almost any defect or void, in preparation for an assembly via a molecular kind of bonding with the substrate (8).

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